Amendments to the Specification:

Please add the following paragraphs beginning at page 4, line 15 of the specification:

Figure 6 is a schematic representation of a multilayer structure with alternate superposed first and second layers.

Figure 7 is a schematic representation of a multilayer structure with alternate superposed first and second layers, the first layer being formed by an intermediate metal layer arranged between first and second peripheral layers so as to form a superposition of three layers.

Please replace the paragraph beginning at page 4, line 19 of the specification with the following paragraph:

An optical device reflecting a range of wavelengths comprised between 10 nm and 20 nm comprises alternate superposed first and second layers 6 and 7 (Figure 6). The first layers 6 are made of metal and preferably molybdenum or of metallic compound and preferably molybdenum carbide. The second layers 7 are formed by an amorphous silicon compound chosen from a-Si-H_x, a-Si-CH_x, a-Si-C_x, a-Si-OH_x, a-Si-F_x, a-Si-FH_x, a-Si-N_x, and a-Si-NH_x, x being comprised between 0.01 and 0.3. Thus a radical chosen from -H, -CH, -C, -OH, -F, -FH, -N and -NH is incorporated in the amorphous silicon so as to saturate the dangling bonds in the amorphous silicon. For example, what is meant by a-Si-H_x compound is a compound formed by hydrogenated amorphous silicon, i.e., amorphous silicon in which a predetermined hydrogen content is incorporated. The hydrogen content to be incorporated is situated in the range 1 to 25% of bonded atomic hydrogen.

Please replace the paragraph beginning at page 6, line 27 with the following paragraph:

Each first layer 6 of the optical device can also be formed by an intermediate metal layer 8 arranged between two peripheral layers 9 and 10 (Figure 7). The peripheral layers 9

and 10 can be made of carbide of said metal, and preferably of molybdenum carbide. The peripheral layers 9 and 10 can also be made of boron carbide, carbon, or nitride of said metal. Thus, according to the invention, a stacking formed by an alternation of first and second layers 6 and 7 can be of the type MY/M/MY/a-Si-H_x, B_4C/M/B_4C/a-Si-H_x or C/M/C/a-Si-H_x, M being a metal, MY being a metallic compound such as a carbide or a nitride of said metal and C being carbon. Thus, as an example, the layer of Mo_2C is replaced by three superposed layers, respectively of Mo_2C, Mo, and Mo_2C, the whole having a total thickness of 2.8 nm. This presents the advantage of improving the optical reflectivity compared with a Mo_2C/a-Si-H_x, stacking, while keeping a mechanical stability over a temperature range of up to 350 C. A similar result is obtained when the Mo_2C layer is replaced by three superposed layers respectively of B_4C, Mo and B_4C.